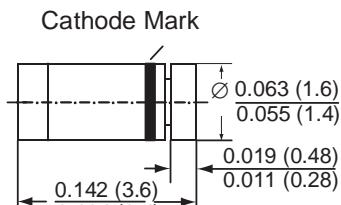
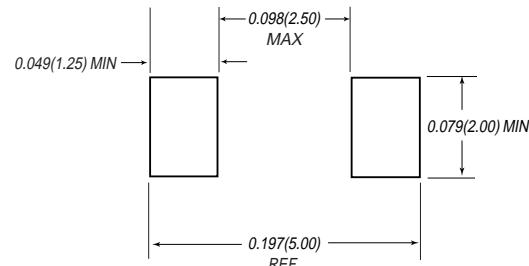


## Voltage Stabilizers


**MiniMELF (SOD-80C)**

*Dimensions in inches and (millimeters)*
**Mounting Pad Layout**


### Mechanical Data

**Case:** MiniMELF Glass Case (SOD-80C)

**Weight:** approx. 0.05g

**Cathode band color:** Blue

**Packaging codes/options:**

 D1/10K per 13" reel (8mm tape), 20K/box  
 D2/2.5K per 7" reel (8mm tape), 20K/box

### Features

- Silicon Planar Stabilizer Diodes
- Monolithic integrated analog circuits in MiniMELF case, designed for small power stabilizer and limitation circuits, providing low dynamic resistance and high-quality stabilization performance as well as low noise. In the reverse direction, these devices show the behavior of forward-biased silicon diodes.
- The end of the device marked with the cathode ring is to be connected: LL1.5 and LL2 to the negative pole of the supply voltage; LL2.4 thru LL5.1 to the positive pole of the supply voltage
- These diodes are also available in DO-35 case with the type designation ZTE1.5 ... ZTE 5.1.

### Maximum Ratings

(TA = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Operating Current (see Table "Characteristics")			
Inverse Current	IF	100	mA
Power dissipation at T <sub>amb</sub> = 25°C	P <sub>tot</sub>	300 <sup>(1)</sup>	W
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature range	T <sub>S</sub>	-55 to +150	°C

### Electrical and Thermal Characteristics

(TA = 25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at IF = 10mA	V <sub>F</sub>	-	-	1.1	V
Temperature Coefficient of the stabilized voltage at Iz = 5mA	$\alpha_{VZ}$	-	-26	-	$10^{-4}/^{\circ}\text{C}$
	$\alpha_{VZ}$	-	-34	-	$10^{-4}/^{\circ}\text{C}$
Thermal resistance junction to ambient air	R <sub>θJA</sub>	-	-	400 <sup>(1)</sup>	°C/W

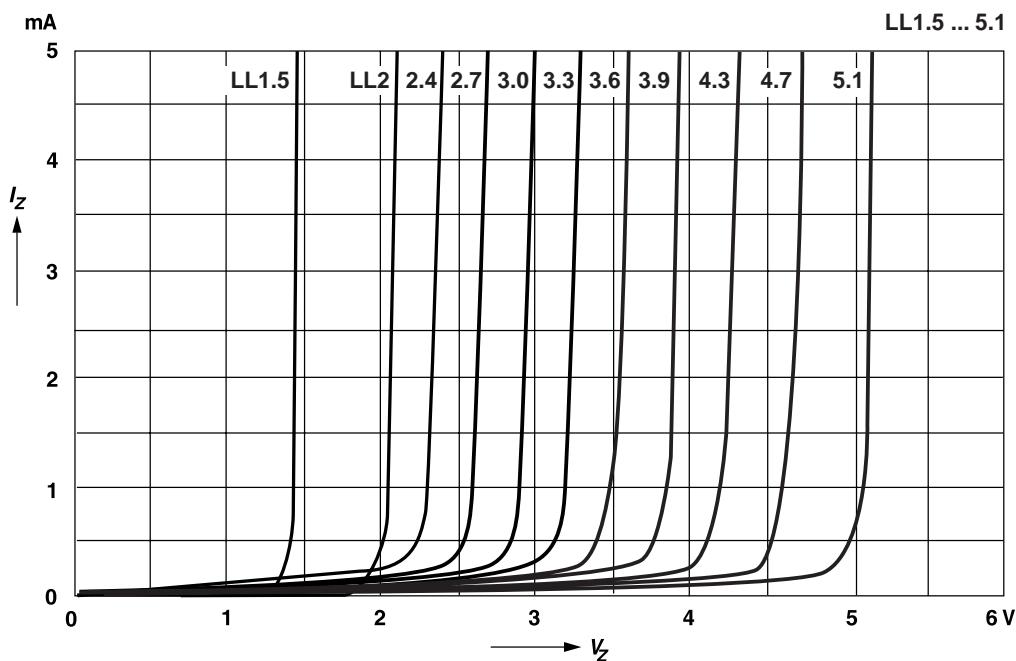
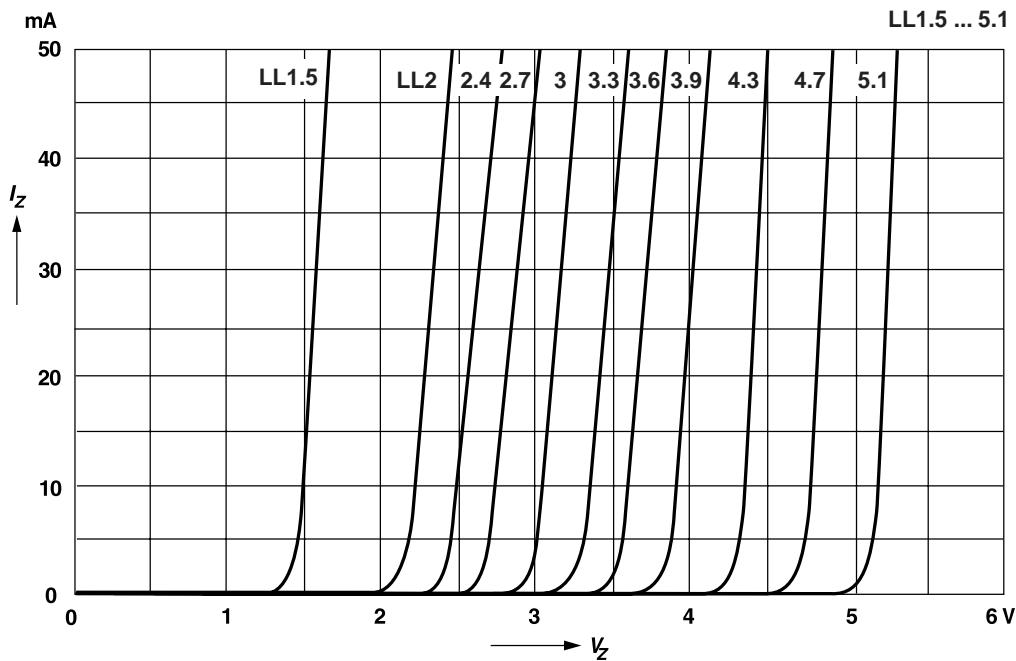
**Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Type	Operating Voltage at $I_Z = 5\text{mA}^{(2)}$ $V_Z (\Omega)$	Dynamic resistance at $I_Z = 5\text{mA}$ $r_{Zj} (\Omega)$	Permissible operating current at $T_{\text{amb}} = 25^\circ\text{C}^{(1)}$ $I_Z \text{ max. (mA)}$
LL1.5	1.35 ... 1.55	13(<20)	120
LL2	2.0 ... 2.3	18(<30)	120
LL2.4	2.2 ... 2.56	14(<20)	120
LL2.7	2.5 ... 2.9	15(<20)	105
LL3	2.8 ... 3.2	15(<20)	95
LL3.3	3.1 ... 3.5	16(<20)	90
LL3.6	3.4 ... 3.8	16(<25)	80
LL3.9	3.7 ... 4.1	17(<25)	75
LL4.3	4.0 ... 4.6	17(<25)	65
LL4.7	4.4 ... 5.0	18(<25)	60
LL5.1	4.8 ... 5.4	18(<25)	55

**Notes:** (1) Valid provided that electrodes are kept at ambient temperature at a distance of 8mm from case

(2) Tested with pulses  $t_p = 5\text{ms}$

**Ratings and  
Characteristic Curves** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

**Breakdown characteristics**
 $T_j = \text{constant (pulsed)}$ 

**Breakdown characteristics**
 $T_j = \text{constant (pulsed)}$ 


# LL1.5 thru LL5.1

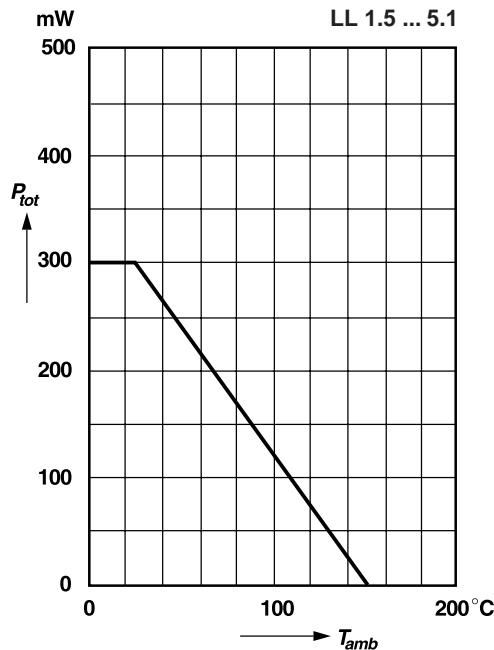


Vishay Semiconductors  
formerly General Semiconductor

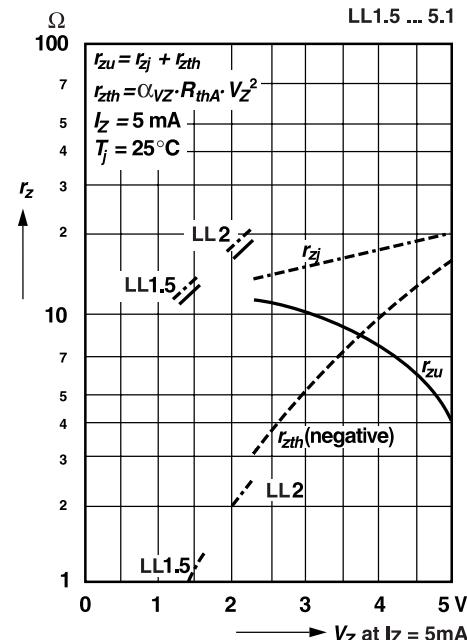
## Ratings and Characteristic Curves ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

### Admissible power dissipation versus ambient temperature

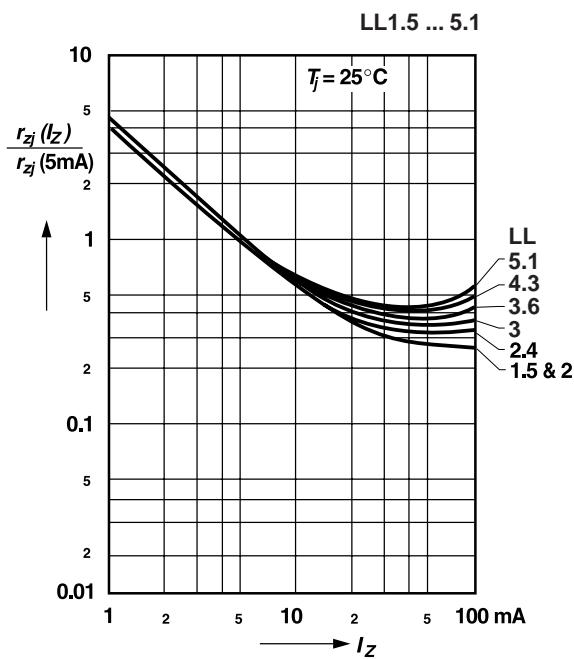
Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature



### Dynamic resistance versus operating voltage



### Dynamic resistance versus operating current, normalized



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Datasheets for electronics components.